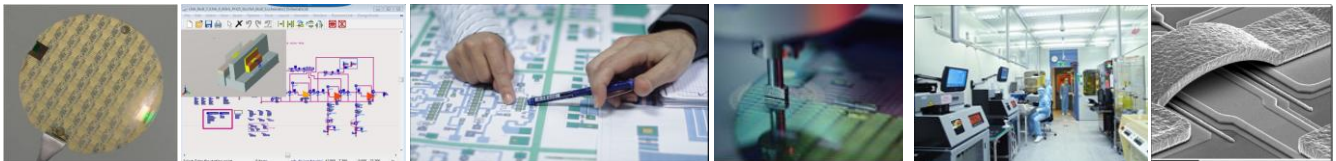




Try GaN **GH25** MPW

With UMS EUROPEAN LEADER
in RF MMIC products and foundry services



UMS launches a shared foundry run on its **GH25** GaN process.

GH25 is a space evaluated 0.25µm HEMT GaN on SiC substrate technology for very high power applications. With GH25, you will be able to design your own GaN HPAs, LNAs, switches, diodes, MMICs, power bars and multi-function components. You will be supported by excellent PDK and models:

- ☒ highly accurate non-linear scalable models supporting electro-thermal capabilities,
- ☒ Stack for EM simulators,
- ☒ DRC for layout rules verification.

Offer conditions and price:

This offer is dedicated to new design concept evaluation and prototyping. The price is valid for engineering die with no screening and no test inspection.

Entry price: 2 800€/mm² for a minimum of 4mm²

The Multi-Project Wafer launch date is **14th of June, 2019.**

INFORMATION	For engineering purpose only. Simply provide your GDS file before June 7, 2019			
DELIVERY	16 Engineering chips, from a PCM tested wafer.			
CONDITIONING	Gel-Pak® box			
AVAILABLE DIE SIZE (mm)	1	2	3	4
MAX RATIO	1:4			

Die size include 70µm dicing street – No optical inspection, no test on MMIC.

Minimum order is 4mm² - Order to be placed before May 15, 2019

Important Notes:

UMS may cancel the run in case of insufficient number of participants.

For some countries a specific dedicated export license may be required before delivery.



How many dies will I receive and how much does it cost?

You will receive 16 engineering chips (untested and without visual inspection) of your circuit in Gel-Pack® box from a **GH25** PCM good wafer. The price is based on your circuit dimensions on the mask tile multiplied by the mm² unit price. For example, if your circuit is 2 x 2 mm², the price is (2 x 2) x 2800€ = 11 200€

GH25 MPW tile dimensions (mm)

1	1	2	3	4
1	1	2	3	4
2	2	4	6	8
3	3	6	9	12
4	4	8	12	16

GH25 mask tile with available die size (mm)

Main characteristics of GH25:

Process	GH25 High Power GaN on SiC
Active Device	HEMT
Power density	4.5W/mm
Gate Length	0.25µm
Ids (gm max) Idss sat /Ic	0.75A/mm 1A/mm
Vbds/Vbce	>120V
Cut off freq.	30GHz
Vpinch	-3.4V
Gm	300mS/mm
VdsDC	25V
Max freq use	≈20GHz for PA
MIM Cap.@ 1 MHz	Density (pF/mm ²) 250
TaN Resistor	Sheet Resistance (Ω/□): 30
TiWSi Resistor	Sheet Resistance (Ω/□): 1000

How to participate to this shared foundry run?

More information? Ordering your GaN area ? Acquisition of the GaN PDK ?
Contact UMS marketing & sales department at mktsales@ums-gaas.com.

